

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
14 July 2005 (14.07.2005)

PCT

(10) International Publication Number
WO 2005/064356 A2

(51) International Patent Classification⁷: **G01R 31/30**,
33/09, 15/20, G11C 11/15

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(21) International Application Number:
PCT/IB2004/052857

(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

(22) International Filing Date:
20 December 2004 (20.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03104937.2 23 December 2003 (23.12.2003) EP
04105805.8 16 November 2004 (16.11.2004) EP

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,
SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

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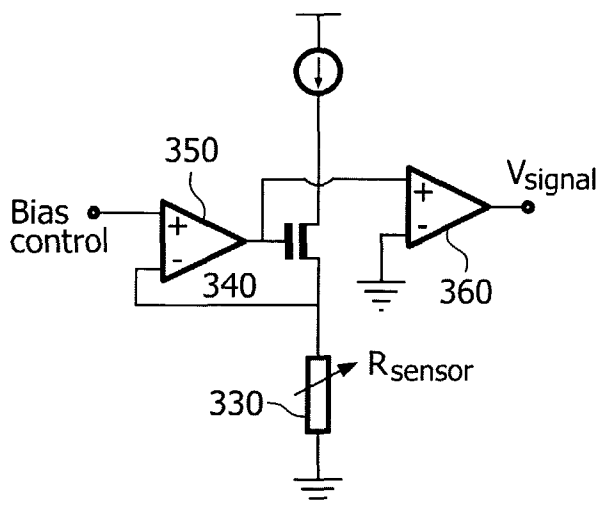
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Declaration under Rule 4.17:

— as to applicant's entitlement to apply for and be granted
a patent (Rule 4.17(ii)) for the following designations AE,
AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ,
CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE,
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PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY,

[Continued on next page]

(54) Title: HIGH SENSITIVITY MAGNETIC BUILT-IN CURRENT SENSOR



(57) Abstract: A sensor for contactlessly detecting
currents, has a sensor element having a magnetic
tunnel junction (MTJ), and detection circuitry, the
sensor element having a resistance which varies
with the magnetic field, and the detection circuitry is
arranged to detect a tunnel current flowing through the
tunnel junction. The sensor element may share an MTJ
stack with memory elements. Also it can provide easy
integration with next generation CMOS processes,
including MRAM technology, be more compact, and
use less power. Solutions for increasing sensitivity
of the sensor, such as providing a flux concentrator,
and for generating higher magnetic fields with a same
current, such as forming L-shaped conductor elements,
are given. The greater sensitivity enables less post
processing to be used, to save power for applications
such as mobile devices. Applications include current
sensors, built-in current sensors, and IDDQ and IDDT
testing, even for next generation CMOS processes.

WO 2005/064356 A2



TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Published:

— without international search report and to be republished upon receipt of that report

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